

BD675A/677A/679A/681

Medium Power Linear and Switching Applications

- Medium Power Darlington TR
- Complement to BD676A, BD678A, BD680A and BD682 respectively



NPN Epitaxial Silicon Transistor

1. Emitter 2.Collector 3.Base

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter		Value	Units	
V _{CBO}	Collector-Base Voltage	: BD675A	45	V	
		: BD677A	60	V	
		: BD67 <mark>9A</mark>	80	V	
	A THE PARTY OF THE	: BD681	100	V	
V _{CEO}	Collector-Emitter Voltage	: BD675A	45	V	
020	750	: BD677A	60	V	
	W.W.W.	: BD679A	80	V	
	MA	: BD681	100	V	
V _{EBO}	Emitter-Base Voltage		5	V	
Ic	Collector Current (DC)		4	Α	
I _{CP}	*Collector Current (Pulse)	6	A		
I _B	Base Current	100	mA		
P _C	Collector Dissipation (T _C =25°C	40	W		
TJ	Junction Temperature	150	°C		
T _{STG}	Storage Temperature	- 65 ~ 150	°C		

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Param	eter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	*Collector-Emitter Sustaini	ing Voltage : BD675A : BD677A : BD679A : BD681	I _C = 50mA, I _B = 0	45 60 80 100	—	#1 t	V V V
I _{CBO}	Collector-Base Voltage	: BD675A : BD677A : BD679A : BD681	$V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, V_{BE} = 0$	E W	WW.	200 200 200 200	μΑ μΑ μΑ μΑ
I _{CEO}	Collector Cut-off Current	: BD675A : BD677A : BD679A : BD681	$V_{CE} = 45V, V_{BE} = 0$ $V_{CE} = 60V, V_{BE} = 0$ $V_{CE} = 80V, V_{BE} = 0$ $V_{CE} = 100V, V_{BE} = 0$			500 500 500 500	μΑ μΑ μΑ μΑ
I _{EBO}	Emitter Cut-off Current	1979	$V_{EB} = 5V, I_{C} = 0$			2	m/
h _{FE}	* DC Current Gain	: BD675A/677A/679A : BD681	$V_{CE} = 3V, I_{C} = 2A$ $V_{CE} = 3V, I_{C} = 1.5A$	750 750			
V _{CE} (sat)	* Collector-Emitter Saturat	ion Voltage : BD675A/677A/679A : BD681	I _C = 2A, I _B = 40mA I _C = 1.5A, I _B = 30mA			2.8 2.5	V
V _{BE} (on) ⊏	* Base-Emitter ON Voltage	: BD675A/677A/679A : BD681	$V_{CE} = 3V, I_{C} = 2A$ $V_{CE} = 3V, I_{C} = 1.5A$			2.5 2.5	V V

Typical Characteristics

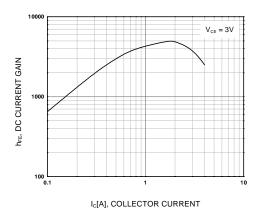


Figure 1. DC current Gain

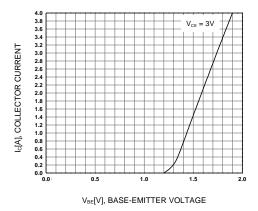


Figure 3. Base-Emitter On Voltage

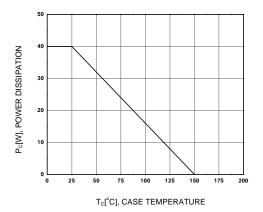


Figure 5. Power Derating

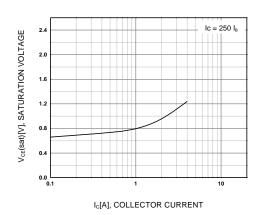
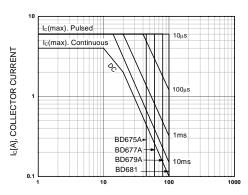


Figure 2. Collector-Emitter Saturation Voltage



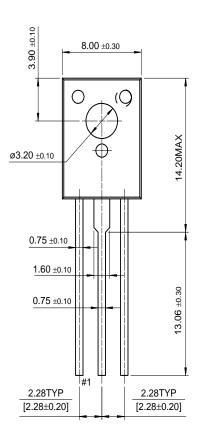
V_{CE}[V], COLLECTOR-EMITTER VOLTAGE

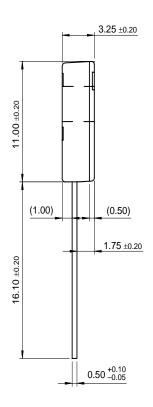
Figure 4. Safe Operating Area

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Package Demensions

TO-126





Dimensions in Millimeters

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